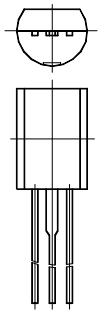
Transys Electronics LIMITED

TO-92MOD Plastic-Encapsulated Transistors

2SB764 TRANSISTOR (PNP)

TO-92MOD



1. EMITTER
2. COLLECTOR
3. BASE

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FEATURES

Power dissipation

P_{CM}: 0.9 W (Tamb=25℃)

Collector current

I_{CM}: -1 A

Collector-base voltage

$V_{(BR)CBO}$: -60 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-10μA, I_E=0	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA, I_B=0	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-10μA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-50V, I_E=0			-1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-4V, I_C=0			-1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-2V, I_C=-50mA	60		320	
	$h_{FE(2)}$	V_{CE}=-2V, I_C=-1A	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=-50mA			-0.7	V
Base-emitter saturation voltage	$V_{BE\ sat}$	I_C=-500mA, I_B=-50mA			-1.2	V
Transition frequency	f_T	V_{CE}=-10V, I_C=-50mA		150		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz		20		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	D	E	F
Range	60-120	100-200	160-320